

## CORRECTION

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Cite this: *Nanoscale*, 2023, **15**, 14267

## Correction: Synaptic plasticity and non-volatile memory characteristics in TiN-nanocrystal-embedded 3D vertical memristor-based synapses for neuromorphic systems

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DOI: 10.1039/d3nr90165c  
[rsc.li/nanoscale](https://rsc.li/nanoscale)

Correction for 'Synaptic plasticity and non-volatile memory characteristics in TiN-nanocrystal-embedded 3D vertical memristor-based synapses for neuromorphic systems' by Seyeong Yang *et al.*, *Nanoscale*, 2023, <https://doi.org/10.1039/D3NR01930F>.

One of the grant numbers given in the original article (2020M3F3A2A01082593) should instead be as follows: 2021M3F3A2A02037889. The acknowledgements of the manuscript should therefore read:

"This research was supported by the National R&D Program through the National Research Foundation of Korea (NRF) funded by the Ministry of Science and ICT under grants 2021M3F3A2A02037889 and 2021M3F3A2A01037927."

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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